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# SBCP53-16T1G

onsemi

Bipolar Transistors - BJT SS GP XSTR PNP 80V

Any questions, please feel free to contact us. info@kaimte.com

## PNP Silicon Epitaxial Transistors

This PNP Silicon Epitaxial transistor is designed for use in audio amplifier applications. The device is housed in the SOT–223 package which is designed for medium power surface mount applications.

- High Current
- NPN Complement is BCP56
- The SOT-223 Package can be soldered using wave or reflow. The formed leads absorb thermal stress during soldering, eliminating the possibility of damage to the die
- Device Marking: BCP53T1G = AH BCP53-10T1G = AH-10 BCP53-16T1G = AH-16
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS** (T<sub>C</sub> = $25^{\circ}$ C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	-80	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	-100	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current	Ι <sub>C</sub>	1.5	Adc
Total Power Dissipation @ $T_A = 25^{\circ}C$ (Note 1) Derate above $25^{\circ}C$	P <sub>D</sub>	1.5 12	W mW/°C
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 sq. in.

#### THERMAL CHARACTERISTICS

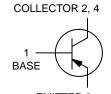
Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction-to-Ambient (Surface Mounted)	$R_{\theta JA}$	83.3	°C/W
Lead Temperature for Soldering, 0.0625″ from case Time in Solder Bath	ΤL	260 10	°C s



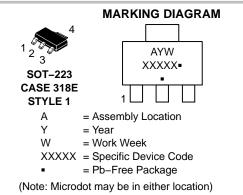
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### MEDIUM POWER HIGH CURRENT SURFACE MOUNT PNP TRANSISTORS



EMITTER 3



#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
BCP53T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
SBCP53-10T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
BCP53-10T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
SBCP53-10T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
BCP53-16T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
SBCP53-16T1G	SOT-223 (Pb-Free)	1000/Tape & Reel
BCP53-16T3G	SOT-223 (Pb-Free)	4000/Tape & Reel
NSVBCP53-16T3G	SOT-223 (Pb-Free)	4000/Tape & Reel

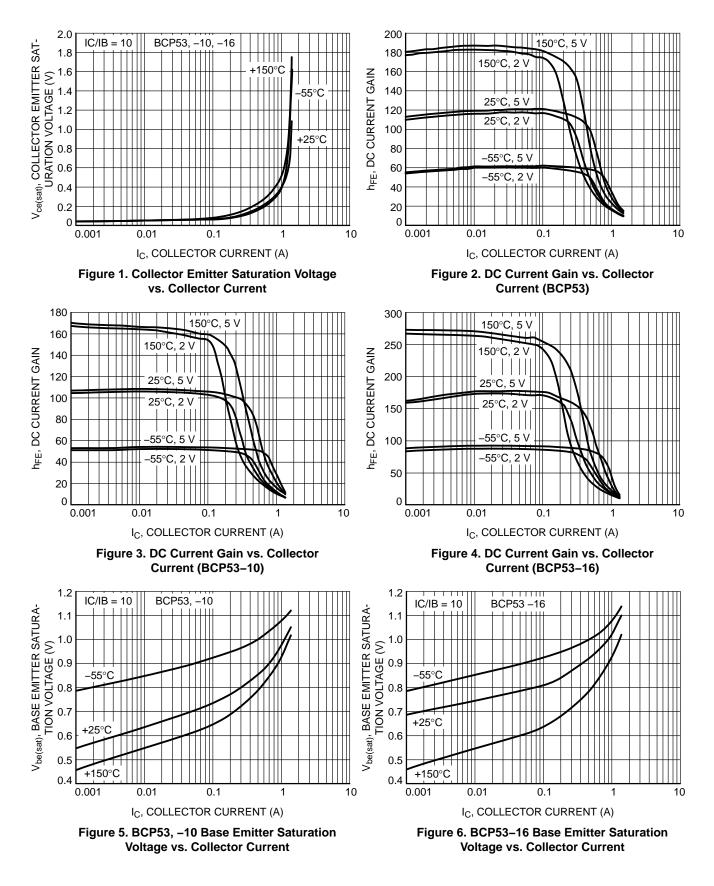
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

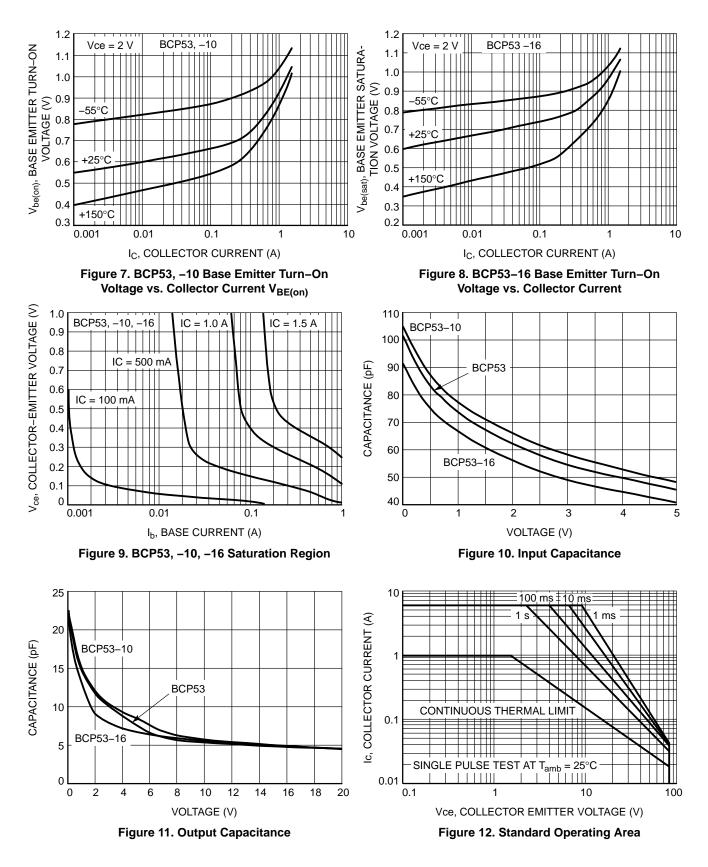
Characteristics	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	· · ·				
Collector–Base Breakdown Voltage $(I_C = -100 \ \mu Adc, I_E = 0)$	V <sub>(BR)CBO</sub>	-100	_	-	Vdc
Collector–Emitter Breakdown Voltage $(I_C = -1.0 \text{ mAdc}, I_B = 0)$	V <sub>(BR)CEO</sub>	-80	_	-	Vdc
Collector–Emitter Breakdown Voltage ( $I_C = -100 \ \mu Adc, R_{BE} = 1.0 \ k\Omega$ )	V <sub>(BR)CER</sub>	-100	_	-	Vdc
Emitter–Base Breakdown Voltage $(I_E = -10 \ \mu Adc, I_C = 0)$	V <sub>(BR)EBO</sub>	-5.0	_	-	Vdc
Collector-Base Cutoff Current ( $V_{CB} = -30$ Vdc, $I_E = 0$ )	I <sub>CBO</sub>	_	_	-100	nAdc
Emitter–Base Cutoff Current ( $V_{EB} = -5.0 \text{ Vdc}, I_C = 0$ )	I <sub>EBO</sub>	_	-	-100	nAdc
ON CHARACTERISTICS					
$\begin{array}{l} \text{DC Current Gain} \\ (I_{C} = -5.0 \text{ mAdc}, V_{CE} = -2.0 \text{ Vdc}) \\ \text{All Part Types} \\ (I_{C} = -150 \text{ mAdc}, V_{CE} = -2.0 \text{ Vdc}) \\ \text{BCP53}, \text{SBCP53} \\ \text{BCP53-10}, \text{SBCP53-10} \\ \text{BCP53-16}, \text{SBCP53-16}, \text{NSVBCP53-16} \\ (I_{C} = -500 \text{ mAdc}, V_{CE} = -2.0 \text{ Vdc}) \\ \text{All Part Types} \end{array}$	h <sub>FE</sub>	25 40 63 100 25		- 250 160 250 -	-
Collector–Emitter Saturation Voltage $(I_C = -500 \text{ mAdc}, I_B = -50 \text{ mAdc})$	V <sub>CE(sat)</sub>	_	-	-0.5	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = -500 mAdc, V <sub>CE</sub> = -2.0 Vdc)	V <sub>BE(on)</sub>	_	-	-1.0	Vdc
DYNAMIC CHARACTERISTICS	· · ·				
Current–Gain – Bandwidth Product ( $I_C = -10$ mAdc, $V_{CE} = -5.0$ Vdc, f = 35 MHz)	fT	_	50	_	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

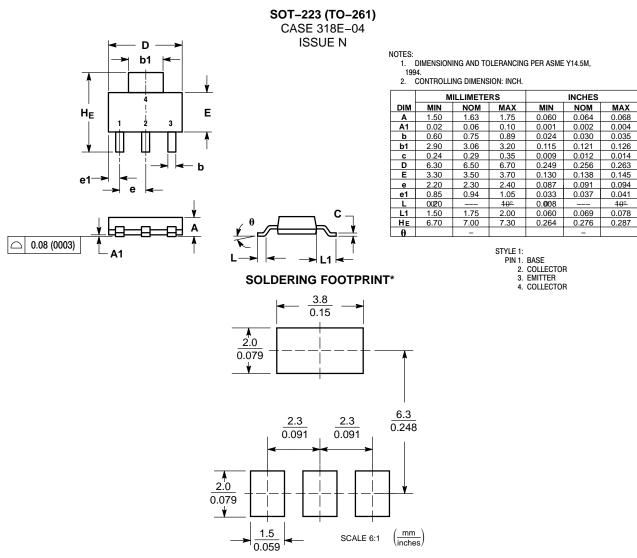
#### **TYPICAL CHARACTERISTICS**



#### **TYPICAL CHARACTERISTICS**



#### PACKAGE DIMENSIONS



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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